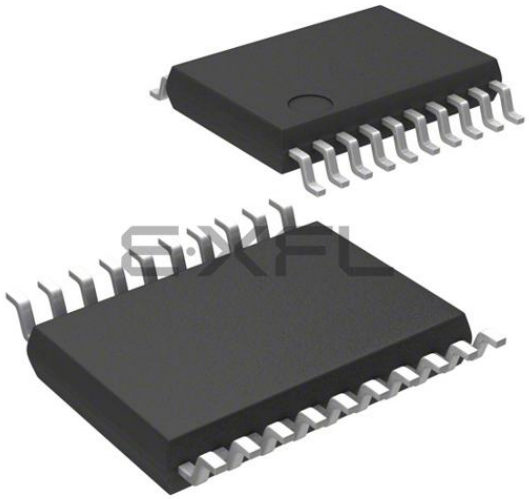

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	640 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.95V ~ 5.5V
Data Converters	A/D 5x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8s103f3p6tr

2 Description

The STM8S103F2/x3 access line 8-bit microcontrollers offer 8 Kbyte Flash program memory, plus integrated true data EEPROM. The STM8S microcontroller family reference manual (RM0016) refers to devices in this family as low-density. They provide the following benefits: performance, robustness, and reduced system cost.

Device performance and robustness are ensured by advanced core and peripherals made in a state-of-the art technology, a 16 MHz clock frequency, robust I/Os, independent watchdogs with separate clock source, and a clock security system.

The system cost is reduced thanks to an integrated true data EEPROM for up to 300 k write/erase cycles and a high system integration level with internal clock oscillators, watchdog and brown-out reset.

Full documentation is offered as well as a wide choice of development tools.

Table 1. STM8S103F2/x3 access line features

Device	STM8S103K3	STM8S103F3	STM8S103F2
Pin count	32	20	20
Maximum number of GPIOs (I/Os)	28	16	16
Ext. interrupt pins	27	16	16
Timer CAPCOM channels	7	7	7
Timer complementary outputs	3	2	2
A/D converter channels	4	5	5
High sink I/Os	21	12	12
Low density Flash program memory (bytes)	8K	8K	4K
Data EEPROM (bytes)	640(1)	640(1)	640(1)
RAM (bytes)	1K	1K	1K
Peripheral set	Multipurpose timer (TIM1), SPI, I2C, UART window WDG, independent WDG, ADC, PWM timer (TIM2), 8-bit timer (TIM4)		

1. No read-while-write (RWW) capability.

4 Product overview

The following section provides an overview of the basic features of the device functional modules and peripherals.

For more detailed information please refer to the corresponding family reference manual (RM0016).

4.1 Central processing unit STM8

The 8-bit STM8 core is designed for code efficiency and performance.

It contains 6 internal registers which are directly addressable in each execution context, 20 addressing modes including indexed indirect and relative addressing and 80 instructions.

Architecture and registers

- Harvard architecture,
- 3-stage pipeline,
- 32-bit wide program memory bus - single cycle fetching for most instructions,
- X and Y 16-bit index registers - enabling indexed addressing modes with or without offset and read-modify-write type data manipulations,
- 8-bit accumulator,
- 24-bit program counter - 16-Mbyte linear memory space,
- 16-bit stack pointer - access to a 64 K-level stack,
- 8-bit condition code register - 7 condition flags for the result of the last instruction.

Addressing

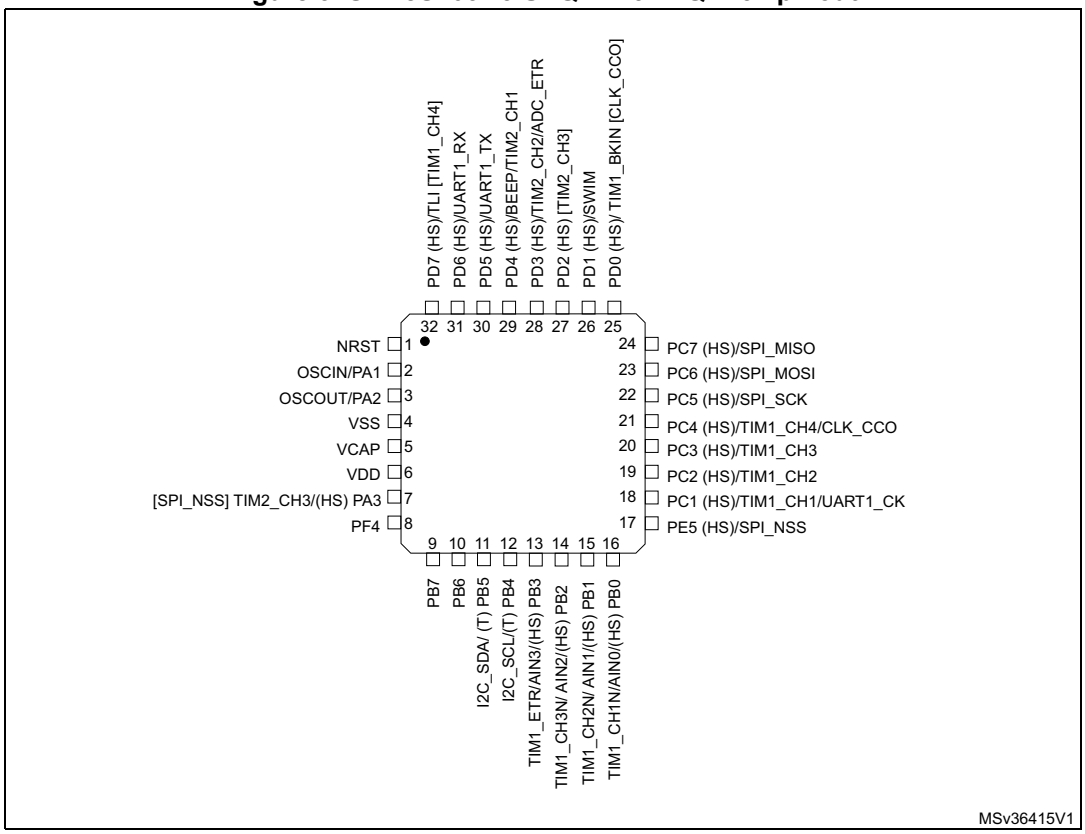
- 20 addressing modes,
- Indexed indirect addressing mode for look-up tables located anywhere in the address space,
- Stack pointer relative addressing mode for local variables and parameter passing.

Instruction set

- 80 instructions with 2-byte average instruction size,
- Standard data movement and logic/arithmetic functions,
- 8-bit by 8-bit multiplication,
- 16-bit by 8-bit and 16-bit by 16-bit division,
- Bit manipulation,
- Data transfer between stack and accumulator (push/pop) with direct stack access,
- Data transfer using the X and Y registers or direct memory-to-memory transfers.

5.1 STM8S103K3 UFQFPN32/LQFP32/SDIP32 pinout and pin description

Figure 3. STM8S103K3 UFQFPN32/LQFP32 pinout

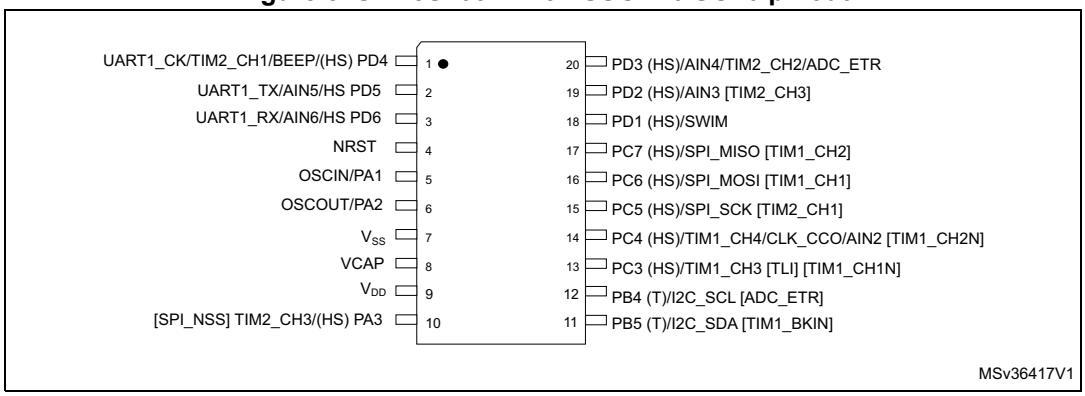


1. (HS) high sink capability.
2. (T) True open drain (P-buffer and protection diode to V_{DD} not implemented).
3. [ ] alternate function remapping option (if the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function).

5.2 STM8S103F2/F3 TSSOP20/SO20/UFQFPN20 pinout and pin description

5.2.1 STM8S103F2/F3 TSSOP20/SO20 pinout

Figure 5. STM8S103F2/F3 TSSOP20/SO20 pinout



1. HS high sink capability.
2. (T) True open drain (P-buffer and protection diode to VDD not implemented).
3. [ ] alternate function remapping option (If the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function)

6.2 Register map

6.2.1 I/O port hardware register map

Table 7. I/O port hardware register map

Address	Block	Register label	Register name	Reset status
0x00 5000	Port A	PA_ODR	Port A data output latch register	0x00
0x00 5001		PA_IDR	Port A input pin value register	0xXX(1)
0x00 5002		PA_DDR	Port A data direction register	0x00
0x00 5003		PA_CR1	Port A control register 1	0x00
0x00 5004		PA_CR2	Port A control register 2	0x00
0x00 5005	Port B	PB_ODR	Port B data output latch register	0x00
0x00 5006		PB_IDR	Port B input pin value register	0xXX(1)
0x00 5007		PB_DDR	Port B data direction register	0x00
0x00 5008		PB_CR1	Port B control register 1	0x00
0x00 5009		PB_CR2	Port B control register 2	0x00
0x00 500A	Port C	PC_ODR	Port C data output latch register	0x00
0x00 500B		PB_IDR	Port C input pin value register	0xXX(1)
0x00 500C		PC_DDR	Port C data direction register	0x00
0x00 500D		PC_CR1	Port C control register 1	0x00
0x00 500E		PC_CR2	Port C control register 2	0x00
0x00 500F	Port D	PD_ODR	Port D data output latch register	0x00
0x00 5010		PD_IDR	Port D input pin value register	0xXX(1)
0x00 5011		PD_DDR	Port D data direction register	0x00
0x00 5012		PD_CR1	Port D control register 1	0x02
0x00 5013		PD_CR2	Port D control register 2	0x00
0x00 5014	Port E	PE_ODR	Port E data output latch register	0x00
0x00 5015		PE_IDR	Port E input pin value register	0xXX(1)
0x00 5016		PE_DDR	Port E data direction register	0x00
0x00 5017		PE_CR1	Port E control register 1	0x00
0x00 5018		PE_CR2	Port E control register 2	0x00
0x00 5019	Port F	PF_ODR	Port F data output latch register	0x00
0x00 501A		PF_IDR	Port F input pin value register	0xXX(1)
0x00 501B		PF_DDR	Port F data direction register	0x00
0x00 501C		PF_CR1	Port F control register 1	0x00
0x00 501D		PF_CR2	Port F control register 2	0x00

1. Depends on the external circuitry.

Table 8. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5250	TIM1	TIM1_CR1	TIM1 control register 1	0x00
0x00 5251		TIM1_CR2	TIM1 control register 2	0x00
0x00 5252		TIM1_SMCR	TIM1 slave mode control register	0x00
0x00 5253		TIM1_ETR	TIM1 external trigger register	0x00
0x00 5254		TIM1_IER	TIM1 interrupt enable register	0x00
0x00 5255		TIM1_SR1	TIM1 status register 1	0x00
0x00 5256		TIM1_SR2	TIM1 status register 2	0x00
0x00 5257		TIM1_EGR	TIM1 event generation register	0x00
0x00 5258		TIM1_CCMR1	TIM1 capture/compare mode register 1	0x00
0x00 5259		TIM1_CCMR2	TIM1 capture/compare mode register 2	0x00
0x00 525A		TIM1_CCMR3	TIM1 capture/compare mode register 3	0x00
0x00 525B		TIM1_CCMR4	TIM1 capture/compare mode register 4	0x00
0x00 525C		TIM1_CCER1	TIM1 capture/compare enable register 1	0x00
0x00 525D		TIM1_CCER2	TIM1 capture/compare enable register 2	0x00
0x00 525E		TIM1_CNTRH	TIM1 counter high	0x00
0x00 525F		TIM1_CNTRL	TIM1 counter low	0x00
0x00 5260		TIM1_PSCRH	TIM1 prescaler register high	0x00
0x00 5261		TIM1_PSCRL	TIM1 prescaler register low	0x00
0x00 5262		TIM1_ARRH	TIM1 auto-reload register high	0xFF
0x00 5263		TIM1_ARRL	TIM1 auto-reload register low	0xFF
0x00 5264		TIM1_RCR	TIM1 repetition counter register	0x00
0x00 5265		TIM1_CCR1H	TIM1 capture/compare register 1 high	0x00
0x00 5266		TIM1_CCR1L	TIM1 capture/compare register 1 low	0x00
0x00 5267		TIM1_CCR2H	TIM1 capture/compare register 2 high	0x00
0x00 5268		TIM1_CCR2L	TIM1 capture/compare register 2 low	0x00
0x00 5269		TIM1_CCR3H	TIM1 capture/compare register 3 high	0x00

Table 8. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5400	ADC1 cont'd	ADC_CSR	ADC control/status register	0x00
0x00 5401		ADC_CR1	ADC configuration register 1	0x00
0x00 5402		ADC_CR2	ADC configuration register 2	0x00
0x00 5403		ADC_CR3	ADC configuration register 3	0x00
0x00 5404		ADC_DRH	ADC data register high	0xXX
0x00 5405		ADC_DRL	ADC data register low	0xXX
0x00 5406		ADC_TDRH	ADC Schmitt trigger disable register high	0x00
0x00 5407		ADC_TDRL	ADC Schmitt trigger disable register low	0x00
0x00 5408		ADC_HTRH	ADC high threshold register high	0x03
0x00 5409		ADC_HTRL	ADC high threshold register low	0xFF
0x00 540A		ADC_LTRH	ADC low threshold register high	0x00
0x00 540B		ADC_LTRL	ADC low threshold register low	0x00
0x00 540C		ADC_AWSRH	ADC analog watchdog status register high	0x00
0x00 540D		ADC_AWSRL	ADC analog watchdog status register low	0x00
0x00 540E		ADC _AWCRH	ADC analog watchdog control register high	0x00
0x00 540F		ADC_AWCRL	ADC analog watchdog control register low	0x00
0x00 5410 to 0x00 57FF	Reserved area (1008 byte)			

1. Depends on the previous reset source.
2. Write-only register.

Table 10. Interrupt mapping (continued)

IRQ no.	Source block	Description	Wakeup from halt mode	Wakeup from active-halt mode	Vector address
21	Reserved	-	-	-	0x00 805C
22	ADC1	ADC1 end of conversion/ analog watchdog interrupt	-	-	0x00 8060
23	TIM4	TIM4 update/ overflow	-	-	0x00 8064
24	Flash	EOP/WR_PG_DIS	-	-	0x00 8068
Reserved					0x00 806C to 0x00 807C

1. Except PA1.

Total current consumption in halt mode

Table 27. Total current consumption in halt mode at V_{DD} = 5 V

Symbol	Parameter	Conditions	Typ	Max at 85 °C(1)	Max at 85 °C(1)	Unit
$I_{DD(H)}$	Supply current in halt mode	Flash in operating mode, HSI clock after wakeup	63	75	105	µA
		Flash in power-down mode, HSI clock after wakeup	6.0	20	55	

1. Guaranteed by characterization results.

Table 28. Total current consumption in halt mode at V_{DD} = 3.3 V

Symbol	Parameter	Conditions	Typ	Max at 85 °C(1)	Max at 85 °C(1)	Unit
$I_{DD(H)}$	Supply current in halt mode	Flash in operating mode, HSI clock after wakeup	60	75	100	µA
		Flash in power-down mode, HSI clock after wakeup	4.5	17	30	

1. Guaranteed by characterization results.

Low power mode wakeup times

Table 29. Wakeup times

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
$t_{WU(WFI)}$	Wakeup time from wait mode to run mode(2)	0 to 16 MHz			-	See note(3)	µs
$t_{WU(WFI)}$	Wakeup time from run mode(2)	f_{CPU}= f_{MASTER}= 16 MHz			0.56	-	
$t_{WU(AH)}$	Wakeup time active halt mode to run mode(2)	MVR voltage regulator on(4)	Flash in operating mode(5)	HSI (after wakeup)	1(6)	2(6)	
$t_{WU(AH)}$	Wakeup time active halt mode to run mode(2)	MVR voltage regulator off(4)	Flash in operating mode(5)	HSI (after wakeup)	3(6)	-	
$t_{WU(AH)}$	Wakeup time active halt mode to run mode(2)	MVR voltage regulator off(4)	Flash in operating mode(5)	HSI (after wakeup)	48(6)	-	
$t_{WU(AH)}$	Wakeup time active halt mode to run mode(2)	MVR voltage regulator off(4)	Flash in power-down mode(5)	HSI (after wakeup)	50(6)	-	
$t_{WU(H)}$	Wakeup time from halt mode to run mode(2)	Flash in operating mode(5)			52	-	
$t_{WU(H)}$	Wakeup time from halt mode to run mode(2)	Flash in power-down mode(5)			54	-	

1. Guaranteed by characterization results.

2. Measured from interrupt event to interrupt vector fetch
3. $t_{WU(WFI)} = 2 \times 1/f_{master} + 67 \times 1/f_{CPU}$
4. Configured by the REGAH bit in the CLK_ICKR register.
5. Configured by the AHALT bit in the FLASH_CR1 register.
6. Plus 1 LSI clock depending on synchronization.

Total current consumption and timing in forced reset state

Table 30. Total current consumption and timing in forced reset state

Symbol	Parameter	Conditions	Typ	Max(1)	Unit
$I_{DD(R)}$	Supply current in reset state(2)	V_{DD} = 5 V	400	-	µA
		V_{DD} = 3.3 V	300	-	
$t_{RESETBL}$	Reset pin release to vector fetch	-	-	150	µs

1. Guaranteed by design.
2. Characterized with all I/Os tied to V_{SS}.

Current consumption of on-chip peripherals

Subject to general operating conditions for V_{DD} and T_A.

HSI internal RC/f_{CPU}= f_{MASTER} = 16 MHz, V_{DD} = 5 V

Table 31. Peripheral current consumption

Symbol	Parameter	Typ	Unit
$I_{DD(TIM1)}$	TIM1 supply current(1)	210	µA
$I_{DD(TIM2)}$	TIM2 supply current(1)	130	
$I_{DD(TIM4)}$	TIM4 supply current(1)	50	
$I_{DD(UART1)}$	UART1 supply current (2)	120	
$I_{DD(SPI)}$	SPI supply current (2)	45	
$I_{DD(I2C)}$	I2C supply current(2)	65	
$I_{DD(ADC1)}$	ADC1 supply current when converting(3)	1000	

1. Data based on a differential I_{DD} measurement between reset configuration and timer counter running at 16 MHz. No IC/OC programmed (no I/O pads toggling). Not tested in production.
2. Data based on a differential IDD measurement between the on-chip peripheral when kept under reset and not clocked and the on-chip peripheral when clocked and not kept under reset. No I/O pads toggling. Not tested in production.
3. Data based on a differential IDD measurement between reset configuration and continuous A/D conversions. Not tested in production.

Current consumption curves

The following figures show typical current consumption measured with code executing in RAM.

Figure 16. Typ $I_{DD(WFI)}$ vs. f_{CPU} HSE external clock, V_{DD} = 5 V

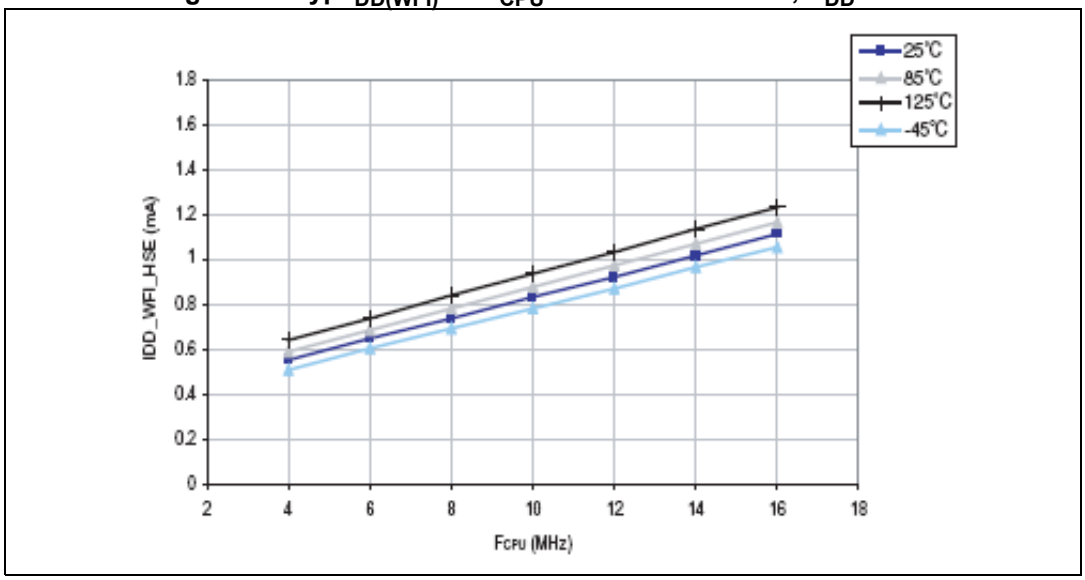
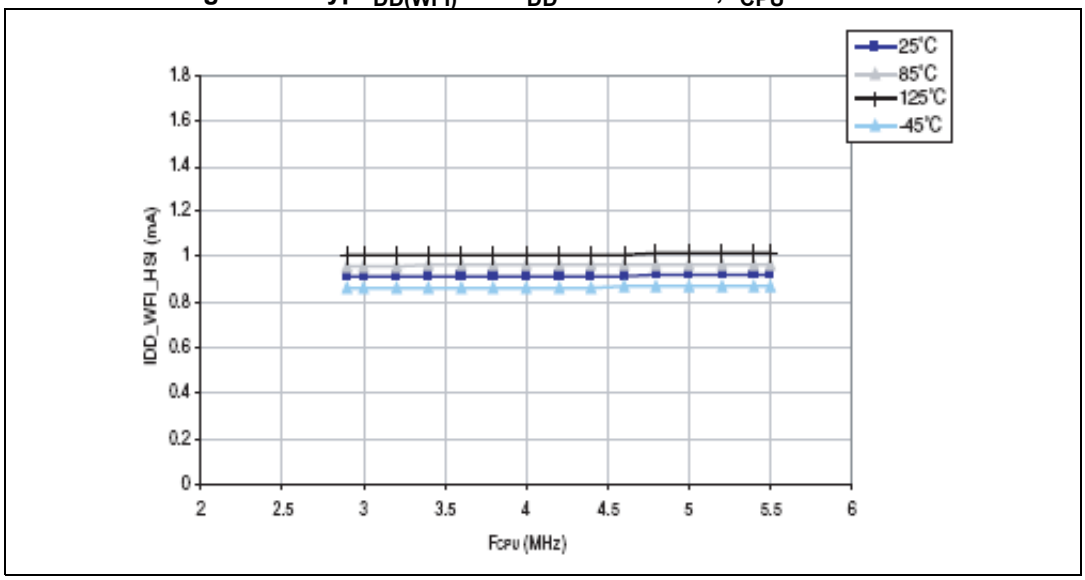


Figure 17. Typ $I_{DD(WFI)}$ vs. V_{DD} HSI RC osc., f_{CPU} = 16 MHz



10.3.10 10-bit ADC characteristics

Subject to general operating conditions for V_{DD}, f_{MASTER}, and T_A unless otherwise specified.

Table 45. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{ADC}	ADC clock frequency	V_{DD}= 2.95 to 5.5 V	1	-	4	MHz
		V_{DD}= 4.5 to 5.5 V	1	-	6	
V_{AIN}	Conversion voltage range(1)	-	V_{SS}	-	V_{DD}	V
C_{ADC}	Internal sample and hold capacitor	-	-	3	-	pF
t_S(1)	Minimum sampling time	f_{ADC} = 4 MHz	-	0.75	-	µs
		f_{ADC} = 6 MHz	-	0.5	-	
t_{STAB}	Wakeup time from standby	-	-	7.0	-	µs
t_{CONV}	Minimum total conversion time (including sampling time, 10-bit resolution)	f_{ADC} = 4 MHz	3.5			µs
		f_{ADC} = 6 MHz	2.33			µs
		-	14			$1/f_{ADC}$

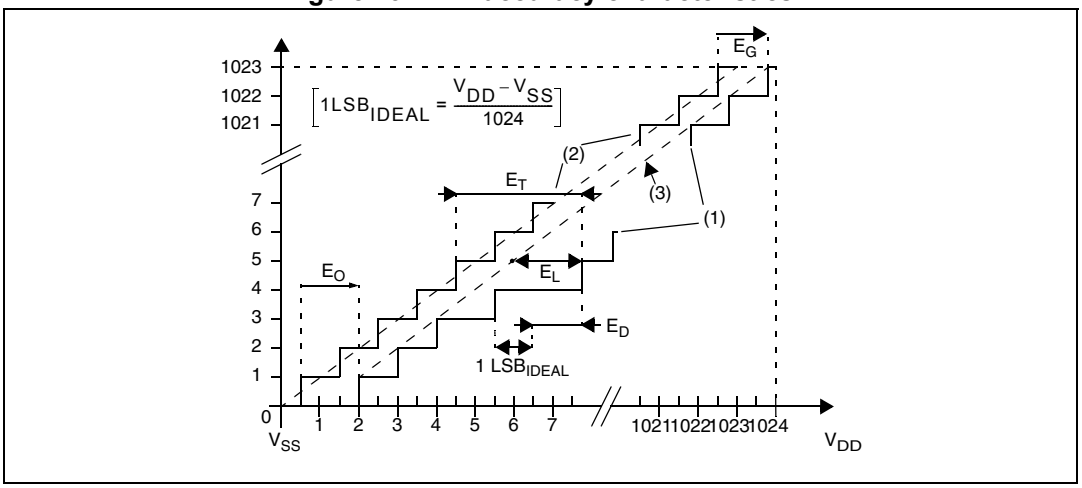
1. During the sample time, the sampling capacitance, C_{AIN} (3 pF max), can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_S. After the end of the sample time t_S, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_S depend on programming.

Table 47. ADC accuracy with R_{AIN}< 10 kΩ, V_{DD}= 3.3 V

Symbol	Parameter	Conditions	Typ	Max(1)	Unit
$\|E_T\|$	Total unadjusted error(2)	f_{ADC} = 2 MHz	1.6	3.5	LSB
		f_{ADC} = 4 MHz	1.9	4	
$\|E_O\|$	Offset error(2)	f_{ADC} = 2 MHz	1	2.5	
		f_{ADC} = 4 MHz	1.5	2.5	
$\|E_G\|$	Gain error(2)	f_{ADC} = 2 MHz	1.3	3	
		f_{ADC} = 4 MHz	2	3	
$\|E_D\|$	Differential linearity error(2)	f_{ADC} = 2 MHz	0.7	1.0	
		f_{ADC} = 4 MHz	0.7	1.5	
$\|E_L\|$	Integral linearity error(2)	f_{ADC} = 2 MHz	0.6	1.5	
		f_{ADC} = 4 MHz	0.8	2	

1. Guaranteed by characterization results.
2. ADC accuracy vs. negative injection current: Injecting negative current on any of the analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 10.3.6* does not affect the ADC accuracy.

Figure 43. ADC accuracy characteristics



1. Example of an actual transfer curve
2. The ideal transfer curve
3. End point correlation line
   E_T = Total unadjusted error: maximum deviation between the actual and the ideal transfer curves.
   E_O = Offset error: deviation between the first actual transition and the first ideal one.
   E_G = Gain error: deviation between the last ideal transition and the last actual one.
   E_D = Differential linearity error: maximum deviation between actual steps and the ideal one.
   E_L = Integral linearity error: maximum deviation between any actual transition and the end point correlation line.

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm IEC 61967-2 which specifies the board and the loading of each pin.

Table 49. EMI data

Symbol	Parameter	Conditions				Unit
		General conditions	Monitored frequency band	Max f_{CPU}(1)		
				16 MHz/ 8 MHz	16 MHz/ 16 MHz	
S_{EMI}	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP32 package. Conforming to IEC 61967-2	0.1 MHz to 30 MHz	5	5	dBµV
			30 MHz to 130 MHz	4	5	
			130 MHz to 1 GHz	5	5	
	EMI level		EMI level	2.5	2.5	-

1. Guaranteed by characterization results.

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD, DLU and LU) using specific measurement methods, the product is stressed to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts x (n+1) supply pin). One model can be simulated: Human body model. This test conforms to the JESD22-A114A/A115A standard. For more details, refer to the application note AN1181.

Table 50. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human body model)	T_A = 25°C, conforming to JESD22-A114	A	4000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charge device model)	T_A= 25°C, conforming to SD22-C101 LQFP32 package	IV	1000	

1. Guaranteed by characterization results

Static latch-up

Two complementary static tests are required on 10 parts to assess the latch-up performance.

- A supply overvoltage (applied to each power supply pin), and
- A current injection (applied to each input, output and configurable I/O pin) are performed on each sample.

This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

Table 51. Electrical sensitivities

Symbol	Parameter	Conditions	Class(1)
LU	Static latch-up class	T_A = 25 °C	A
		T_A = 85 °C	
		T_A = 125 °C	

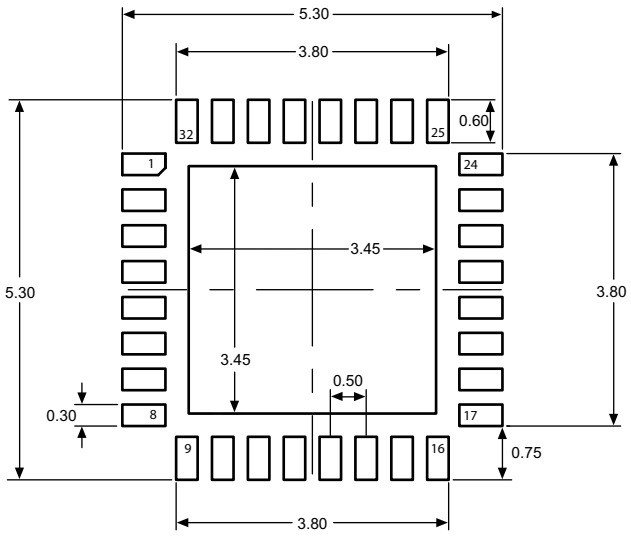
1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to class A it exceeds the JEDEC standard. B class strictly covers all the JEDEC criteria (international standard).

Table 53. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.180	0.230	0.280	0.0071	0.0091	0.0110
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 49. UFQFPN32 - 32-pin, 5 x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Section 11.7: UFQFPN recommended footprint shows the recommended footprints for UFQFPN with and without on-board emulation.

Table 55. SDIP32 package mechanical data (continued)

Dim.	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
eB	-	-	12.700	-	-	0.5000
L	2.540	3.048	3.810	0.1000	0.1200	0.1500

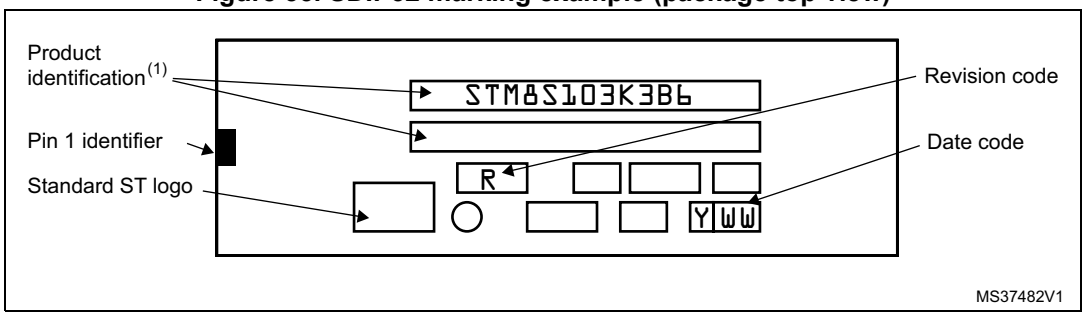
1. Values in inches are converted from mm and rounded to 4 decimal digits

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

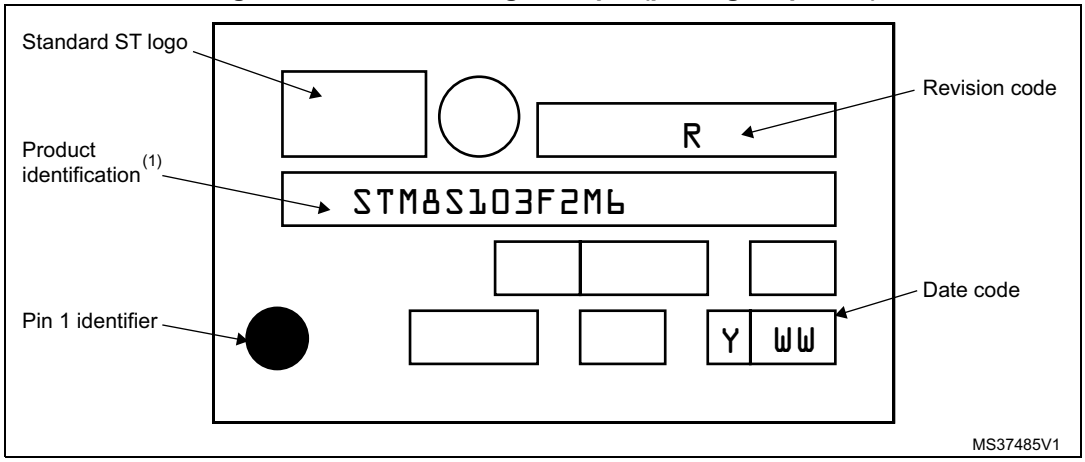
Figure 55. SDIP32 marking example (package top view)



1. Parts marked as “ES”,”E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

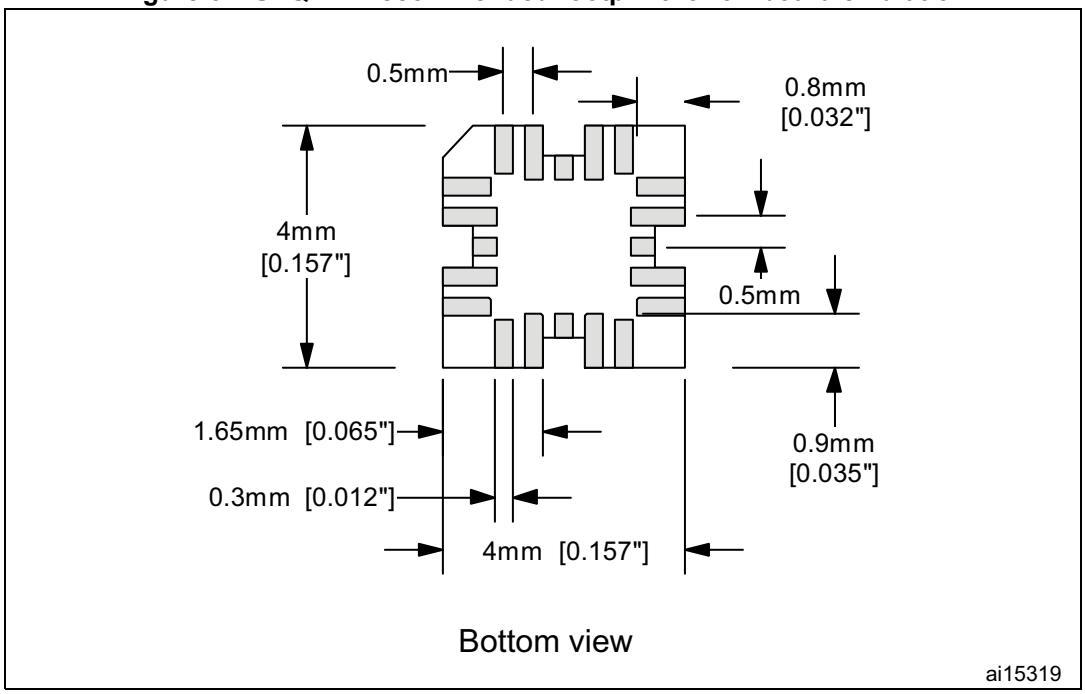
Figure 60. SO20 marking example (package top view)



1. Parts marked as “ES”,”E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

11.7 UFQFPN recommended footprint

Figure 61. UFQFPN recommended footprint for on-board emulation



12 Thermal characteristics

The maximum junction temperature (T_{Jmax}) of the device must never exceed the values specified in *Table 19: General operating conditions*, otherwise the functionality of the device cannot be guaranteed.

The maximum junction temperature T_{Jmax}, in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum ambient temperature in °C
- Θ_{JA} is the package junction-to-ambient thermal resistance in ° C/W
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$)
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum power dissipation on output pins
  Where:
  $P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
  taking into account the actual V_{OL}/I_{OL} and V_{OH}/I_{OH} of the I/Os at low and high level in the application.

Table 58. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient TSSOP20 - 4.4mm	84	°C/W
	Thermal resistance junction-ambient SO20W (300 mils)	91	
	Thermal resistance junction-ambient UFQFPN20 - 3 x 3 mm	90	
	Thermal resistance junction-ambient LQFP32 - 7 x 7 mm	60	
	Thermal resistance junction-ambient UFQFPN32 - 5 x 5 mm	38	
	Thermal resistance junction-ambient SDIP32 - 400 mils	60	

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

12.1 Reference document

JESD51-2 integrated circuits thermal test method environment conditions - natural convection (still air). Available from www.jedec.org.